FDBL9401L-F085

N-Channel Logic Level PowerTrench® MOSFET

40 V, 300 A, 0.55 mΩ

Features

- Typical $R_{DS(on)}$ = 0.47 mΩ at V_{GS} = 10 V, I_D = 80 A
- Typical $Q_{g(tot)}$ = 269 nC at V_{GS} = 10 V, I_D = 80 A
- UIS Capability
- Qualified to AEC Q101
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Automotive Engine Control
- PowerTrain Management
- Solenoid and Motor Drivers
- Integrated Starter/Alternator
- Primary Switch for 12 V Systems

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DSS}	Drain-to-Source Voltage	40	V
V_{GS}	Gate-to-Source Voltage	±20	V
I_D	Drain Current − Continuous, (V_{GS} = 10 V) T_C = 25°C (Note 1)	300	A
	Pulsed Drain Current, T_C = 25°C	(See Figure 4)	A
E_{AS}	Single Pulse Avalanche Energy (Note 2)	913	mJ
P_D	Power Dissipation	429	W
	Derate Above 25°C	2.86	W/°C
T_J, T_{STG}	Operating and Storage Temperature	−55 to +175	°C

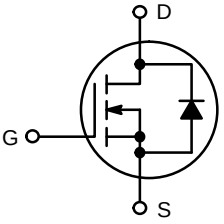
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Current is limited by bondwire configuration.
2. Starting T_J = 25°C, L = 530 μH, I_{AS} = 64 A, V_{DD} = 40 V during inductor charging and V_{DD} = 0 V during time in avalanche.

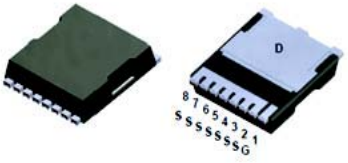
ON Semiconductor®

www.onsemi.com

V_{DSS}	$R_{DS(ON)}$ MAX	I_D MAX
40 V	0.55 mΩ @ 10 V	300 A

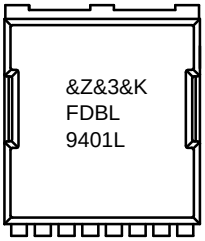


N-CHANNEL MOSFET



H−PSOF8L
CASE 100CU

MARKING DIAGRAM



&Z	= Assembly Plant Code
&3	= Numeric Date Code
&K	= Lot Code
FDBL9401L	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.35	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 3)	43	

3. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design, while $R_{\theta JA}$ is determined by the board design. The maximum rating presented here is based on mounting on a 1 in^2 pad of 2 oz copper.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain-to-Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	40	−	−	V
I_{DSS}	Drain-to-Source Leakage Current	V_{DS} = 40 V, V_{GS} = 0 V T_J = 25°C T_J = 175°C (Note 4)	 − −	 − −	 1 2000	μA
I_{GSS}	Gate-to-Source Leakage Current	V_{GS} = ±20 V	−	−	±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate−to−Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	1	1.7	3	V
$R_{DS(on)}$	Drain−to−Source On Resistance	V_{GS} = 4.5 V, I_D = 80 A	−	0.59	0.76	mΩ
		V_{GS} = 10 V, I_D = 80 A T_J = 25°C T_J = 175°C (Note 4)	 − −	 0.47 0.81	 0.55 0.97	mΩ
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 20 V, V_{GS} = 0 V, f = 1 MHz	−	19550	−	pF
C_{oss}	Output Capacitance		−	5630	−	pF
C_{rss}	Reverse Transfer Capacitance		−	509	−	pF
R_g	Gate Resistance	V_{GS} = 0.5 V, f = 1 MHz	−	2.8	−	Ω
$Q_{g(tot)}$	Total Gate Charge at 10 V	V_{GS} = 0 V to 10 V, V_{DD} = 32 V, I_D = 80 A	−	269	376	nC
$Q_{g(th)}$	Threshold Gate Charge	V_{GS} = 0 V to 1 V, V_{DD} = 32 V, I_D = 80 A	−	17	−	nC
Q_{gs}	Gate−to−Source Gate Charge	V_{DD} = 32 V, I_D = 80 A	−	56	−	nC
Q_{gd}	Gate−to−Drain “Miller” Charge	V_{DD} = 32 V, I_D = 80 A	−	33	−	nC
SWITCHING CHARACTERISTICS						
t_{on}	Turn-On Time	V_{DD} = 20 V, I_D = 80 A, V_{GS} = 10 V, R_{GEN} = 6 Ω	−	−	150	ns
$t_{d(on)}$	Turn-On Delay Time		−	27	−	ns
t_r	Turn-On Rise Time		−	49	−	ns
$t_{d(off)}$	Turn-Off Delay Time		−	196	−	ns
t_f	Turn-Off Fall Time		−	79	−	ns
t_{off}	Turn-Off Time		−	−	412	ns
DRAIN-SOURCE DIODE CHARACTERISTICS						
V_{SD}	Source−to−Drain Diode Voltage	I_{SD} = 80 A, V_{GS} = 0 V	−	0.78	1.25	V
		I_{SD} = 40 A, V_{GS} = 0 V	−	0.74	1	
t_{rr}	Reverse−Recovery Time	I_F = 80 A, dI_{SD}/dt = 100 A/μs	−	130	195	ns
Q_{rr}	Reverse−Recovery Charge		−	270	405	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. The maximum value is specified by design at T_J = 175°C. Product is not tested to this condition in production.

TYPICAL CHARACTERISTICS

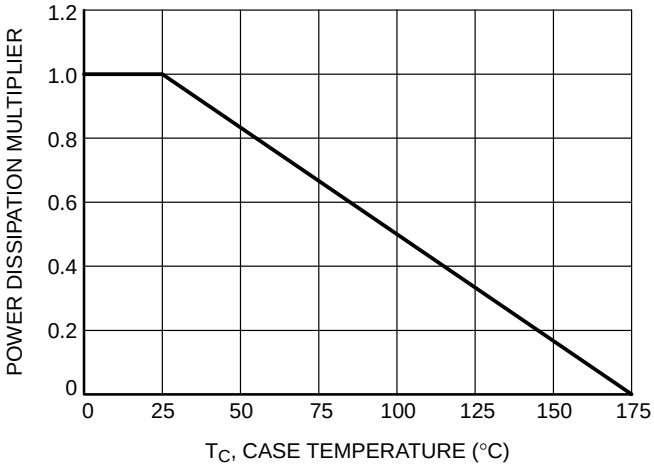


Figure 1. Normalized Power Dissipation vs. Case Temperature

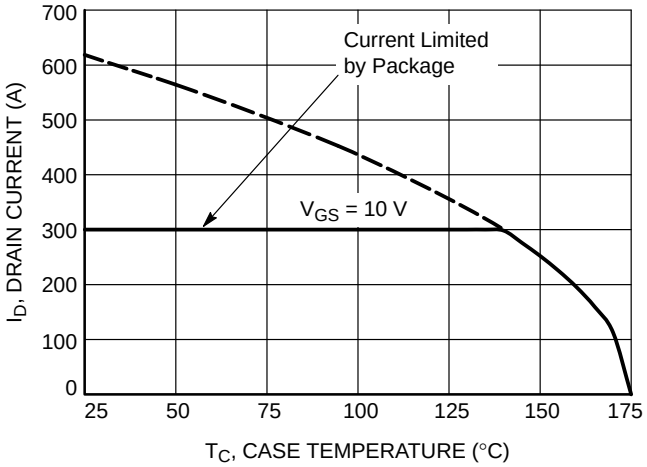


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

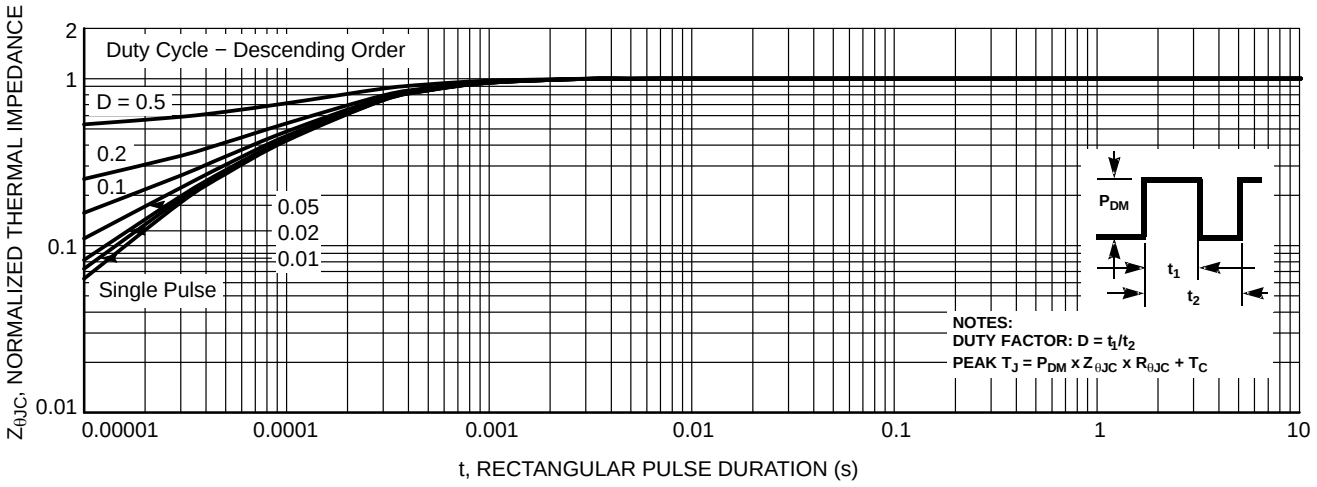


Figure 3. Normalized Maximum Transient Thermal Impedance

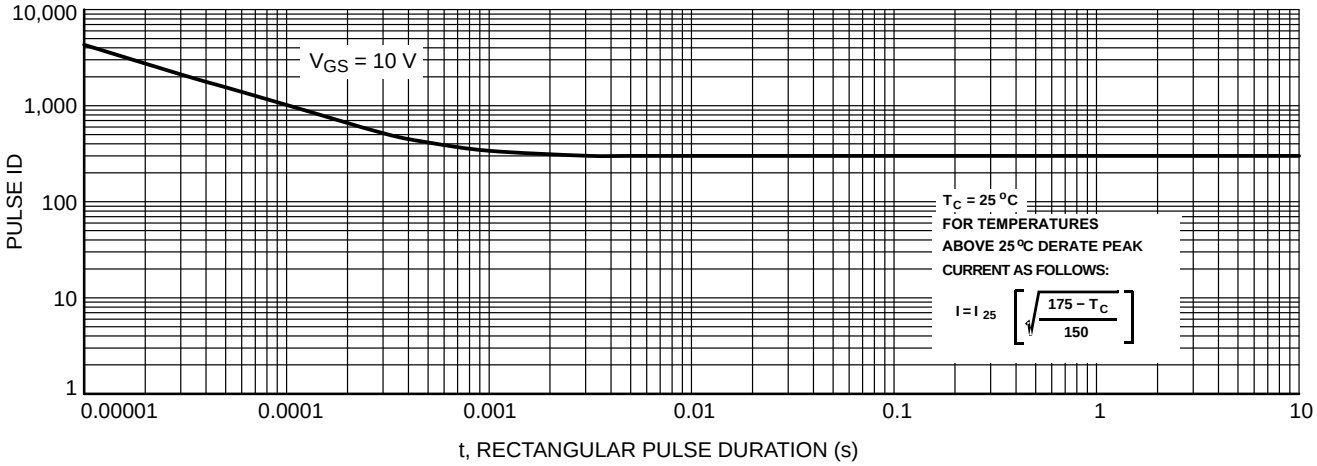


Figure 4. Peak Current Capability

TYPICAL CHARACTERISTICS

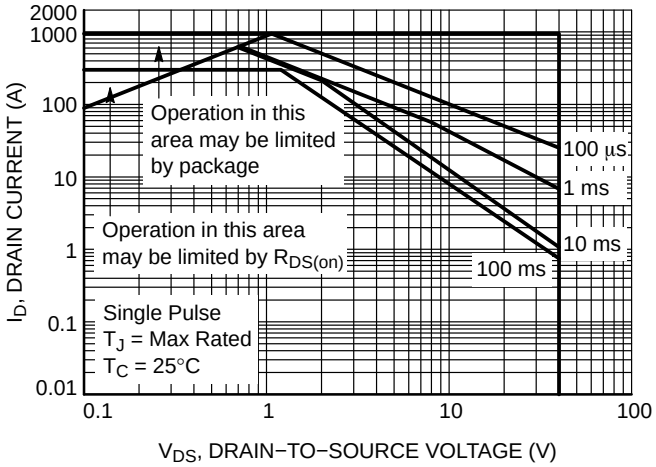


Figure 5. Forward Bias Safe Operating Area

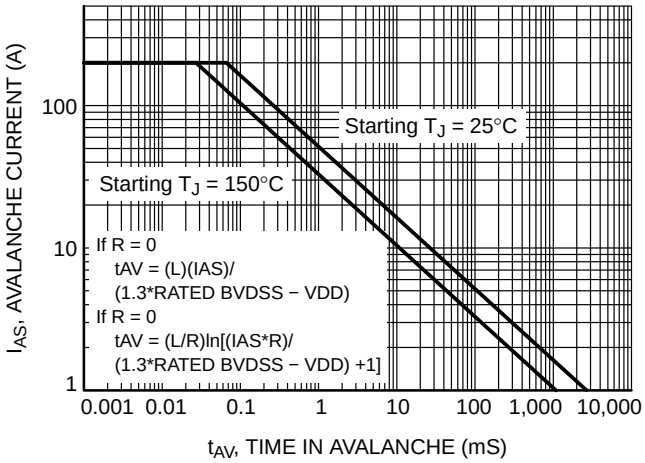


Figure 6. Unclamped Inductive Switching Capability

Note: Refer to ON Semiconductor Application Notes AN7514 and AN7515

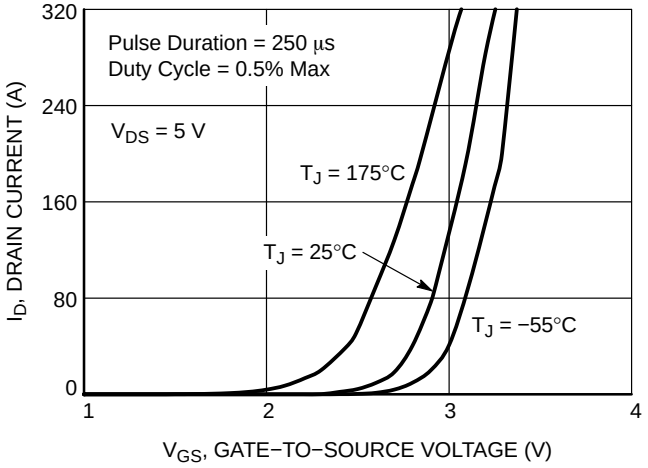


Figure 7. Transfer Characteristics

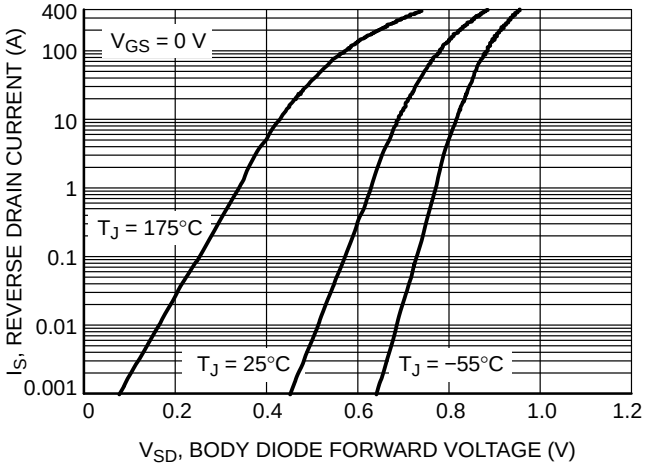


Figure 8. Forward Diode Characteristics

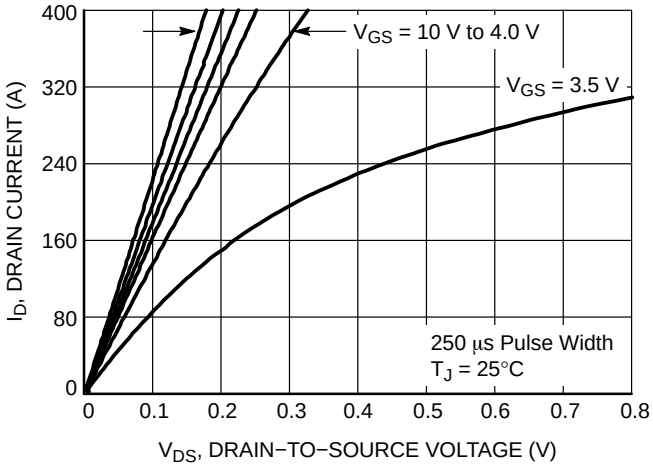


Figure 9. Saturation Characteristics

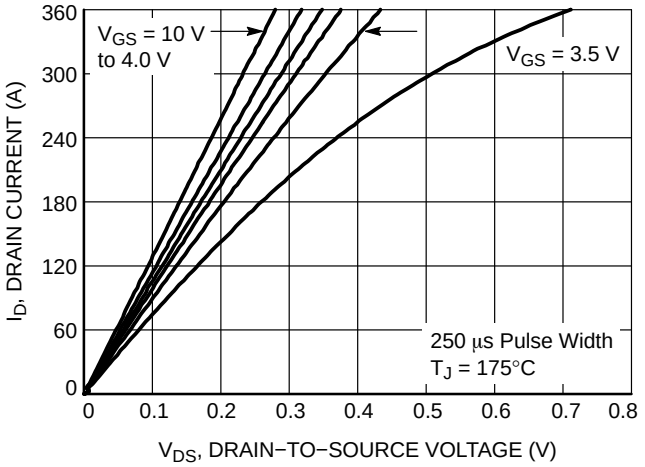


Figure 10. Saturation Characteristics

TYPICAL CHARACTERISTICS

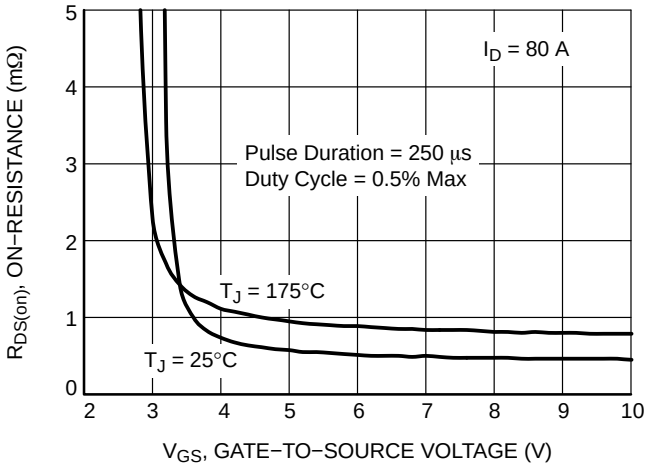


Figure 11. $R_{DS(on)}$ vs. Gate Voltage

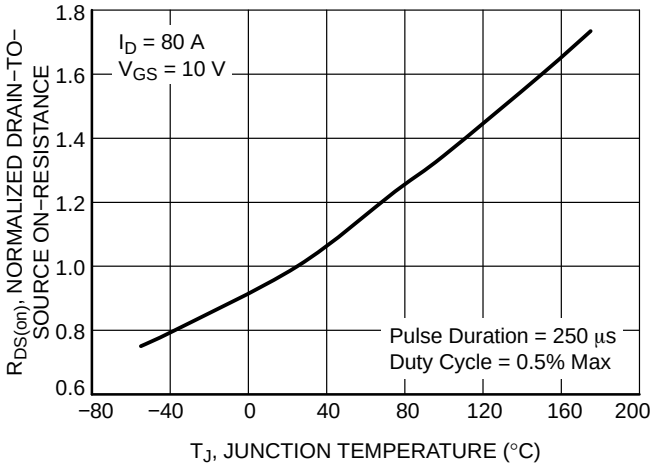


Figure 12. Normalized $R_{DS(on)}$ vs. Junction Temperature

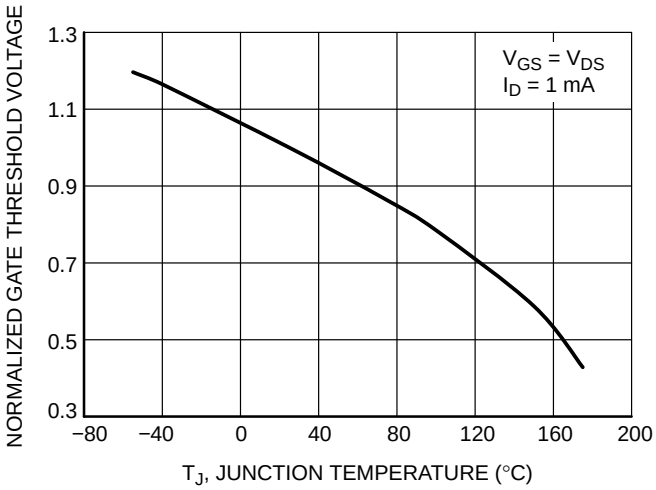


Figure 13. Normalized Gate Threshold Voltage vs. Temperature

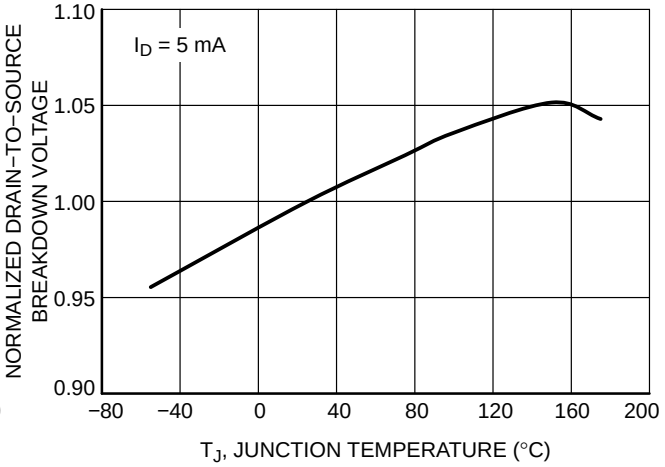


Figure 14. Normalized Drain−to−Source Breakdown Voltage vs. Junction Temperature

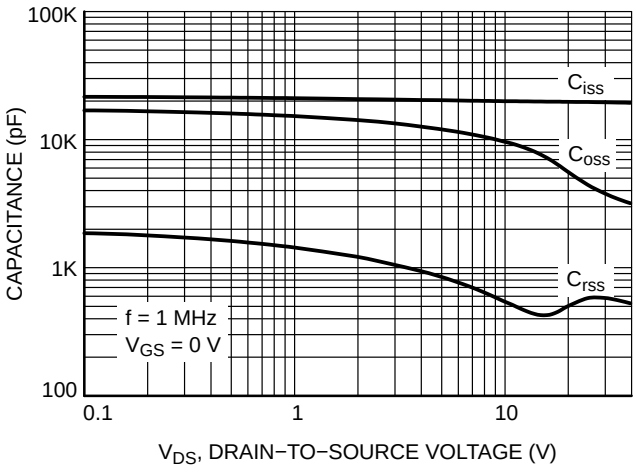


Figure 15. Capacitance vs. Drain−to−Source Voltage

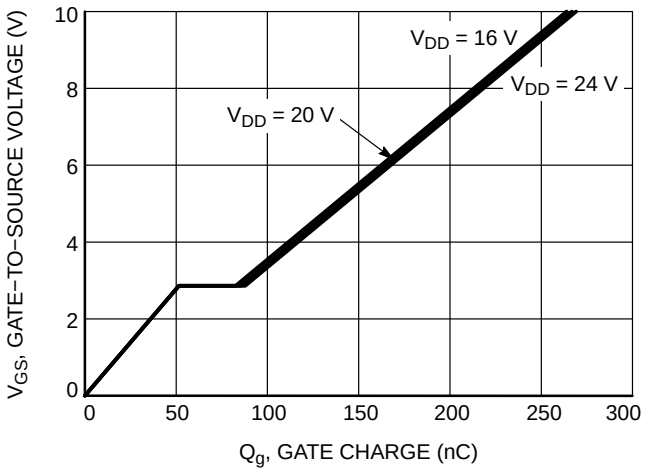
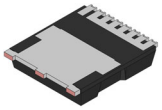


Figure 16. Gate Charge vs. Gate−to−Source Voltage

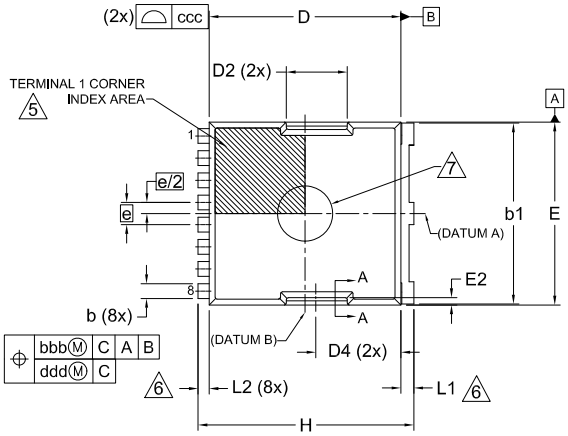
PACKAGE MARKING AND ORDERING INFORMATION

Device	Marking	Package	Reel Size	Tape Width	Quantity
FDBL9401L−F085	FDBL9401L	H−PSOF8L (Pb-Free / Halogen Free)	13″	24 mm	2000 Units

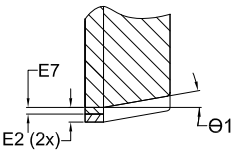


H−PSOF8L 11.68x9.80x2.30, 1.20P
CASE 100CU
ISSUE F

DATE 30 JUL 2024



TOP VIEW



SECTION "A-A"
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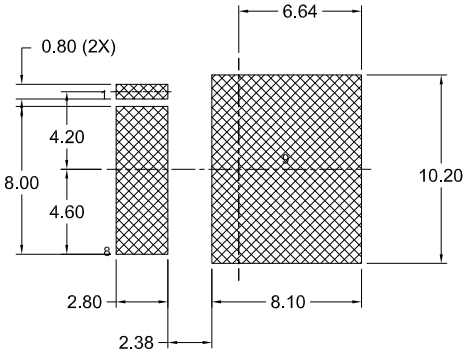
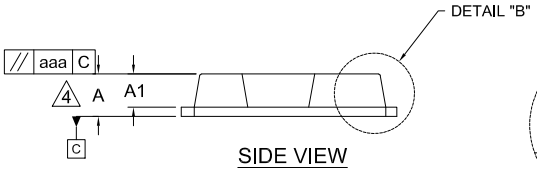
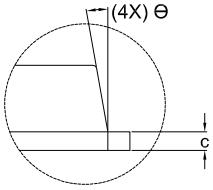


LAND PATTERN RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.



SIDE VIEW



DETAIL "B"
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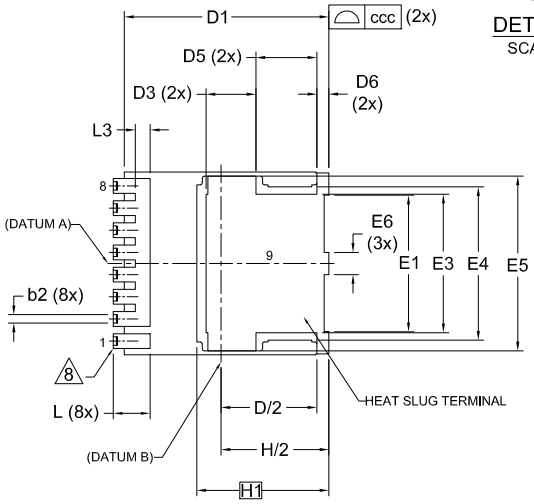


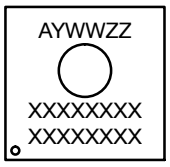
BOTTOM VIEW

NOTES:
1. PACKAGE STANDARD REFERENCE: JEDEC MO-299, ISSUE B.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
3. "e" REPRESENTS THE TERMINAL PITCH.
4. THIS DIMENSION INCLUDES ENCAPSULATION THICKNESS "A1", AND PACKAGE BODY THICKNESS, BUT DOES NOT INCLUDE ATTACHED FEATURES, e.g.,EXTERNAL OR CHIP CAPACITORS. AN INTEGRAL HEATSLUG IS NOT CONSIDERED AS ATTACHED FEATURE.
5. A VISUAL INDEX FEATURE MUST BE LOCATED WITHIN THE HATCHED AREA.
6. DIMENSIONS b1,L1,L2 APPLY TO PLATED TERMINALS.
7. THE LOCATION AND SIZE OF EJECTOR MARKS ARE OPTIONAL.
8. THE LOCATION AND NUMBER OF FUSED LEADS ARE OPTIONAL.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
A1	1.70	1.80	1.90
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.35	0.45	0.55
c	0.40	0.50	0.60
D	10.28	10.38	10.48
D/2	5.09	5.19	5.29
D1	10.98	11.08	11.18
D2	3.20	3.30	3.40
D3	2.60	2.70	2.80
D4	4.45	4.55	4.65
D5	3.20	3.30	3.40
D6	0.55	0.65	0.75
E	9.80	9.90	10.00
E1	7.30	7.40	7.50
E2	0.30	0.40	0.50
E3	7.40	7.50	7.60
E4	8.20	8.30	8.40

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
E5	9.36	9.46	9.56
E6	1.10	1.20	1.30
E7	0.15	0.18	0.21
e	1.20 BSC		
e/2	0.60 BSC		
H	11.58	11.68	11.78
H/2	5.74	5.84	5.94
H1	7.15 BSC		
L	1.90	2.00	2.10
L1	0.60	0.70	0.80
L2	0.50	0.60	0.70
L3	0.70	0.80	0.90
Θ	10° REF		
Θ1	10° REF		
aaa	0.20		
bbb	0.25		
ccc	0.20		
ddd	0.20		
eee	0.10		

GENERIC MARKING DIAGRAM*



A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code
XXXX = Specific Device Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	**98AON13813G**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**H−PSOF8L 11.68x9.80x2.30, 1.20P**	**PAGE 1 OF 1**

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales